Abstracts

Status of InP HEMT Technology for Microwave Receiver Applications (Dec. 1996, Part II [T-MTT])

P.M. Smith. "Status of InP HEMT Technology for Microwave Receiver Applications (Dec. 1996, Part II [T-MTT])." 1996 Transactions on Microwave Theory and Techniques 44.12 (Dec. 1996, Part II [T-MTT] (1996 Symposium Issue)): 2328-2333.

The current status of InP-based high electron mobility transistor (HEMT) technology for low noise amplification at frequencies up to more than 100 GHz is presented. Following a review of recent advances industry-wide in both device and circuit performance, two issues which will pace the rate at which this new technology can be inserted into microwave systems--material/process maturity and long-term reliability--are discussed.

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